Index

adsorption 189, 193
AFM, *see* atomic force microscope
ALD, *see* atomic layer deposition
annealing 99, 146–147, 152, 157, 162–164, 168, 263, 265, 281–282
  high-temperature 144, 146, 162
annealing temperature 9, 146, 159–160, 162–164
Ar preheating 196–198
arsenic donors 15–16
atomic force microscope (AFM) 7, 76–77, 79–80, 83, 91, 93, 95, 97, 101–104, 107, 110–111
atomic layer deposition (ALD) 170
atomic layer doping 181, 183, 200–201, 205, 207–208
atomic layer order 201–202
atomic layers 33, 194, 198, 200, 203, 206, 208
atomic-order surface reaction control 182

bandgap 29, 31, 33–34, 42, 44, 46–47, 50–52, 54, 61, 131, 142, 157, 281
  direct 34, 50
bias temperature instability (BTI) 150–151
bilayer graphene pn junction devices 57
black phosphorus (BP) 59, 61
BP, *see* black phosphorus
BTI, *see* bias temperature instability
buried oxide 12, 16, 105, 218, 226

carbon atoms 31–32, 36, 47
carbon nanotubes 31, 83, 111–112
CD, *see* critical dimension
channel materials 40, 46, 48–49
channel mobility 147–148, 169
charge carriers 32, 51, 54, 57, 78
charge transfer 44
chemical vapor deposition (CVD) 27, 35–37, 60, 100, 112, 182, 266
chemical vapor deposition, low-pressure 181, 208
circuit simulation 216–217, 236–237, 239, 241, 243, 245, 247
CMOS, *see* complementary metal–oxide–semiconductor
CMOS technologies 28, 35, 37, 128–129, 255, 267, 284–285
compact model extractions 217, 229–230, 232
  statistical 215, 232
compact models 217, 219, 229–231, 234, 236
  statistical 233, 236

complementary metal–oxide–semiconductor (CMOS) 3, 5, 253–254, 256, 258, 260, 262, 264, 266, 268, 270, 272, 274, 276, 288
conduction band offset 129, 132
contact resistance 28, 44–45
Coulomb blockade 13–14, 16
Coulomb potentials 11–13
critical dimension (CD) 87, 223, 258, 269–270, 290
Cu foil 36–37, 40
CVD, *see* chemical vapor deposition
CVD graphene 35, 38
CVD process of graphene growth 36–37

dangling bonds 97, 189, 282
DD, *see* drift-diffusion
DD simulations 220–221
design technology co-optimization (DTCO) 215–216
DG, *see* double-gate
diamond 3–4, 16–20
  silicon-vacancy center in 16–17
DIBL, *see* drain-induced barrier lowering
dielectric constant 129, 131–132, 134, 137
  static 131–132
dielectric films 127, 134, 137–138, 156, 169
dielectric scaling 126, 128, 130, 132, 134, 136, 138, 140, 142, 144, 146, 148, 150, 152, 154
dip-pen lithography 113–114
dipole effect 134, 137, 139
dipole formation 44, 135
dipoles 133–135, 137–138
direct self-assembly (DSA) 259, 261, 264
dopant atoms 4
dopants 3–5, 8–10, 13, 15–16
double-gate (DG) 44, 218, 227, 270
drain-induced barrier lowering (DIBL) 141–142, 218, 222–224, 227–228, 232, 269, 278
drift-diffusion (DD) 220–222
DSA, *see* direct self-assembly
DTCO, *see* design technology co-optimization

EBL, *see* electron-beam lithography
electrochemical delamination process 39–40
electron-beam lithography 87, 91–92, 109
electron-beam lithography (EBL) 87, 90–92, 109
electronic devices, graphene-based 42, 61
electronic work function 133, 135–136
electronic work function (EWF) 133, 135–137
EOT
  see equivalent oxide thickness
  function of 139, 153, 157, 165
EOT scaling 152, 154, 162, 165
epitaxial graphene 28, 48
epitaxial growth 182–183, 185, 187, 263
equivalent oxide thickness (EOT) 125, 129, 137–138, 140, 148, 152–154, 157, 160, 162–166, 169, 218
etching 39, 105, 107, 225, 255, 257, 266
  wet 39, 104, 106
EWF, *see* electronic work function

Fermi-level pinning (FLP) 128, 133, 136–137, 142, 144
FET, *see* field-effect transistor
FIB, *see* focused ion beam
field-effect transistor (FET) 4, 10, 12, 28, 31, 40, 42, 47, 105, 126, 253, 270, 283
finFET devices 261
finFETs 154, 160, 215, 217–218, 221–223, 230, 254, 259, 269–271
flatband voltage 135, 137–139
FLP, *see* Fermi-level pinning
focused ion beam (FIB) 6–7, 96, 100, 115

GAA, *see* gate-all-around
gas chromatograph (GC) 287–288
gate-all-around (GAA) 254, 263, 270
gate bias 12, 14, 16, 44, 220
gate dielectric films 125–126, 129, 140, 153, 157, 169
gate dielectric materials 128–129, 169–170
gate dielectrics 126, 133, 140, 147–148, 160, 169
  Hf-based 140–141, 143, 145, 147, 149, 151, 153
gate electrode 12, 110, 134–135, 144, 165–166, 169, 267
gate insulators 126–128
gate leakage 127, 129, 140–141, 151, 153, 156
gate length 48–49, 125, 127, 223–224, 227–228, 230, 237–238, 245, 254, 256, 258, 265, 271–272, 275–276, 279
gate metal 133, 164, 167, 225
gate NW transistors 258
gate oxide 12, 226
gate stacks 137, 141–142, 145–146, 150, 167, 218, 265, 282
  high-κ/metal 140, 145–146, 148–151, 256, 280
GC, *see* gas chromatograph
Ge 7, 31, 37, 170, 181–182, 185, 189, 191, 193–201, 206–209
Ge epitaxial growth 200–201, 203, 205, 207–208
graphene 27–40, 42–49, 51–57, 59, 61, 103
  bilayer 45, 47, 49, 55
  disordered 56
  monolayer 51
  optical micrograph of 39
  optoelectronic applications for 56–57, 59
  structure and properties of 31, 61
  suspended 28, 33
graphene-based devices 56
graphene devices 42
  bilayer 46
graphene FETs 47, 49, 54
graphene growth 35–38
graphene layers 35–36, 45, 47
graphene nanoribbons 33, 46
graphene photodetectors 56
graphene pn junctions 53, 57
graphene research 29, 42
graphene transistors 45
graphene–metal contacts 42, 52
graphene–metal interface 45
graphite 31–32
group IV semiconductors 182–183

hard mask (HM) 218, 263, 265
heterointerface 182, 201, 205
high-κ/metal gate interfaces 137
high-κ/silicon interface 132–133, 135, 154, 165–167, 169

HM, *see* hard mask
hole mobility 50, 273, 276, 279
Hubbard bands 14–15
hybrid-channel CMOS integration 275, 277
hydride gases 182, 193–197, 199
hydrocarbons 36–37
hydrogen annealing 256, 262–263, 278, 280, 282
hydrogen-free surface 195–196
hydrogen-terminated surfaces 185, 196, 198
hydrogen-terminated unreconstructed surface 195–196

Langmuir-type formulation 182, 186
Langmuir-type model 181, 194–196, 208
lanthanum oxide 159
lanthanum silicate 129, 159–162, 165–166, 168
LER, *see* line edge roughness
line edge roughness (LER) 47, 225–226
lithography 79–80, 82–83, 89–90, 96, 98, 103, 106, 108, 110, 112, 225, 255–256, 258
lithography techniques 79, 83, 90, 96–97, 99, 101, 103, 105, 107, 109, 111, 113
  local-probe 79, 113
local oxidation 82, 84, 89, 101–102, 104, 107
low-pressure CVD system 183–184

metal electrodes 42, 165, 167
metal gate 129, 134, 137, 140, 144, 152, 169, 225
metal gate electrodes 165
metal gate granularity (MGG) 225–226, 228–229
metal-induced gap states (MIGS) 137
metal-oxide-semiconductor field-effect transistor (MOSFET) 4, 46–47, 126–128, 140
metal–graphene interface 43–44, 52
metallic substrates, catalytic 38–39
metallic ultrathin films 103, 108–109
metal–metal interface 43
MGG, *see* metal gate granularity
microscopy 76–77, 80, 263
MIGS, *see* metal-induced gap states
Monte Carlo simulations 220–222
MOS capacitors 141, 144, 165–166
MOS transistors 140, 142, 147–148, 153, 170
MOSFET, *see* metal-oxide-semiconductor field-effect transistor
MOSFETs, stacked silicon NW 263, 265

nano-oxidation 106–108, 110
nanotubes 111–112
nanowire ISFET 282–283
nanowire transistors 256, 262, 275–276
nanowires (NWs) 105, 253–257, 261, 263, 265, 267–269, 271, 273, 275–279, 282, 284, 287
nanowires
  circular 281–282
  stacked 277–278, 280
nanowires for sensing devices 282–283, 285, 287, 289
near-field techniques 85–86, 88

NWs, *see* nanowires

optoelectronic applications 38, 61
optoelectronic devices 28, 31, 34

p-FET 276–278
P-FET nanowire transistors 275
photo-thermoelectric effect (PTE) 52–53
photons 17, 51, 54–55, 75
  sensing 50–51, 53, 55
photovoltaic effect (PVE) 52–54, 59
PMA, *see* post-metallization annealing
pn junctions 50, 52, 57, 59
  graphene–silicon 57–58
polymer resist mask 90–91, 93, 95
polysilicon 133, 141–144, 265, 290–291
polysilicon gate electrode 135, 140–141
polysilicon oxidation 144
polysilicon/SiO_2 141, 149
post-metallization annealing (PMA) 162, 164
PTE, *see* photo-thermoelectric effect
PVE, *see* photovoltaic effect

quantum dots 14, 54, 98–99
quantum processing 3–5, 19
quantum transport 12–15, 19

radio-frequency (RF) 33, 38, 42, 47
random discrete dopants (RDDs) 218, 225, 229
RDDs, *see* random discrete dopants
RF, *see* radio-frequency

scanning electron microscopy (SEM) 257, 261
scanning probe microscopes (SPM) 75–77, 79, 81, 90–91, 93, 96, 100, 114
scanning tunneling microscope 76–77, 82
scanning tunneling microscope (STM) 5, 76–77, 79, 82, 97–98, 100
scavenging technique 154
SCEs, *see* short-channel effects
Schottky junction solar cells 58–59
SCs, *see* solar cells
SEM, *see* scanning electron microscopy
semiconducting 31, 33, 46–47, 49
semiconductor devices 4, 9, 61
semiconductor nanowires 253–255, 257, 259, 261, 263, 265, 267
  fabrication of 255, 257, 259, 261, 263, 265, 267
semiconductors 4, 29, 32, 34, 43–44, 129
sensing devices 282–283, 285, 287, 289
short-channel effects (SCEs) 228, 268, 271, 277–278
silicate bonding 156, 158
silicates 131, 155, 157–159, 162
silicon
  crystalline 290–291
  hydrogen-terminated 193, 198, 200
  nitrided 199, 201–202
silicon epitaxial growth 182, 185, 201, 204, 206
silicon MOSFETs 49
silicon nanowires 59, 104, 256, 258, 261–263, 268–269, 271–273, 275–279, 281, 283–284, 286

basic electrical features of 268–269, 271, 273, 275, 277, 279, 281
silicon-on-insulator 104–105, 256, 271
silicon substrate 126, 132, 137, 141, 153, 162, 165, 167, 182, 185
silicon surfaces, hydrogenated 97–98
single-electron transistor 96, 108
single-ion implantation 5, 7, 10–11, 13, 18
single-ion implantation method 4, 6, 9, 12, 15
single-layer graphene 45, 59
SNM, *see* static noise margin
SNM distribution 240, 245–247
solar cells (SCs) 29, 50–51, 59
spectral response (SR) 57–58
SPM, *see* scanning probe microscopes
SPM Lithography 88–90, 95, 111
SR, *see* spectral response
SRAM, *see* static random access memory
SRAM cell 236–237, 242, 246
SS, *see* subthreshold slopes
static noise margin (SNM) 236–249
static random access memory (SRAM) 50, 248, 278
STM, *see* scanning tunneling microscope
subthreshold slopes (SS) 221, 223–224, 227, 269, 278
supercollisions 52–53
superlattice 263, 265
surface, equi-concentration 221
surface modification 80–81, 83
surface roughness 166, 262, 280

TCAD, *see* technology computer-aided design
TCAD simulations 217, 219, 224, 231, 233, 240, 249
technology computer-aided design (TCAD) 216, 226, 238
TEM, *see* transmission electron microscope
test-bed transistors 218–219, 221, 223, 225, 227
TMDs, *see* transition metal dichalcogenides
top-down approach 254–255
transistors 3, 7, 12, 28, 33, 46–50, 223, 243, 253, 269, 271
transition metal dichalcogenides (TMDs) 27–31, 33–35, 40–42, 49–50, 61
transmission electron microscope (TEM) 165, 257, 259, 261
tunnel barriers 99–100, 109
tunnel junctions 95–96, 99, 107
tunneling, single-electron 12–13, 16
two-dimensional materials 27–28, 30, 32, 34, 36, 38, 40, 42–44, 46, 48, 50, 52, 54, 56, 58
two-donor devices 13, 15

uniaxial compressive strain 277, 279

wet etching method 38–39

XPS measurement 159, 202–203, 206

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Simon Deleonibus retired from CEA-LETI on January 1, 2016, as chief scientist after 30 years of research on the architecture of micro- and nanoelectronic devices. Before joining CEA-LETI, he was with Thomson Semiconductors (1981–1986), where he developed and transferred to production advanced microelectronic devices and products. He obtained his PhD in applied physics from Paris University (1982). He is a visiting professor at Tokyo Institute of Technology (Tokyo, Japan) since 2014, National Chiao Tung University (Hsinchu, Taiwan) since 2015, and Chinese Academy of Science (Beijing, PRC) since 2016. A recipient of several awards and honors, and erstwhile associate editor of the *IEEE Transactions on Electron Devices* (2008–2014), Prof. Deleonibus is research director of the CEA since 2002, a distinguished lecturer at IEEE since 2004, and a fellow of the IEEE since 2006 and of the Electrochemical Society since 2015.

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